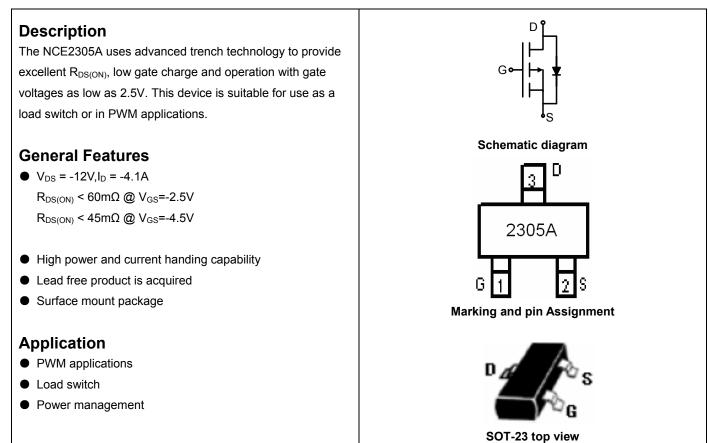


NCE P-Channel Enhancement Mode Power MOSFET



Package Marking And Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
2305A	NCE2305A	SOT-23	Ø180mm	8 mm	3000 units

Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	Vds	-12	V
Gate-Source Voltage	Vgs	±12	V
Drain Current -Continuous	Ι _D	-4.1	A
Drain Current -Pulsed (Note 1)	I _{DM}	-15	А
Maximum Power Dissipation	PD	1.7	W
Operating Junction and Storage Temperature Range	T _J ,T _{STG}	-55 To 150	°C

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient (Note 2)	R _{θJA}	74	°C /W
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Electrical Characteristics (T_A=25[°]Cunless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						



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Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =-250µA	-12	-18	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-12V,V _{GS} =0V	-	-	-1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±12V,V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} ,I _D =-250µA		-0.7	-1.0	V
Drain Course On State Desistance	R _{DS(ON)}	V _{GS} =-4.5V, I _D =-4.1A	-	30	45	mΩ
Drain-Source On-State Resistance		V _{GS} =-2.5V, I _D =-3A	-	43	60	
Forward Transconductance	g fs	V _{DS} =-5V,I _D =-2A	5	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C _{lss}	- V _{DS} =-4V,V _{GS} =0V,	-	740	-	PF
Output Capacitance	C _{oss}	– V _{DS} –-4V,V _{GS} –0V, – F=1.0MHz	-	290	-	PF
Reverse Transfer Capacitance	C _{rss}	- F - 1.0101112	-	190	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}		-	12	-	nS
Turn-on Rise Time	tr	V_{DD} =-4V,I _D =-3.3A,	-	35	-	nS
Turn-Off Delay Time	t _{d(off)}	R_{L} =-1.2 Ω , V_{GEN} =-4.5 V , R_{g} =1 Ω	-	30	-	nS
Turn-Off Fall Time	t _f		-	10	-	nS
Total Gate Charge	Qg		-	7.8	-	nC
Gate-Source Charge	Q _{gs}	V _{DS} =-4V,I _D =-4.1A,V _{GS} =-4.5V	-	1.2	-	nC
Gate-Drain Charge	Q _{gd}		-	1.6	-	nC
Drain-Source Diode Characteristics	·		-		-	•
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =-1.6A	-	-	-1.2	V
Diode Forward Current (Note 2)	I _S		-	-	4.1	Α

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.

2. Surface Mounted on FR4 Board, $t \le 10$ sec.

3. Pulse Test: Pulse Width \leq 300µs, Duty Cycle \leq 2%.

4. Guaranteed by design, not subject to production



NCE2305A



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Typical Electrical and Thermal Characteristics

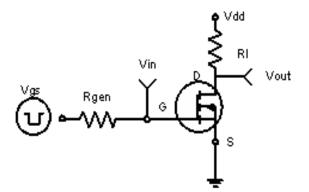
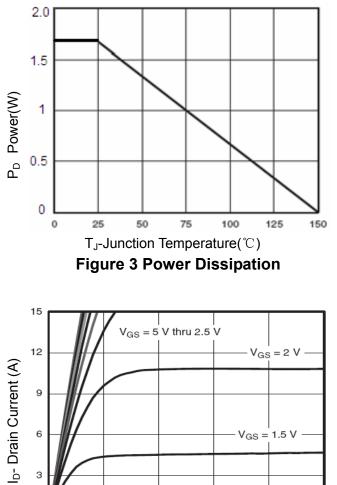
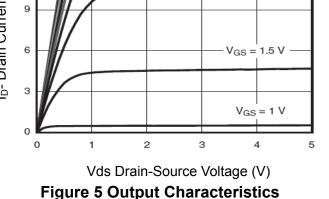
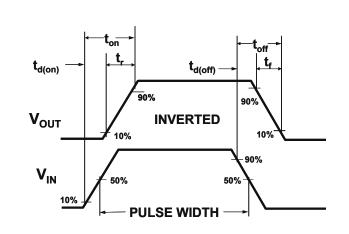


Figure 1:Switching Test Circuit









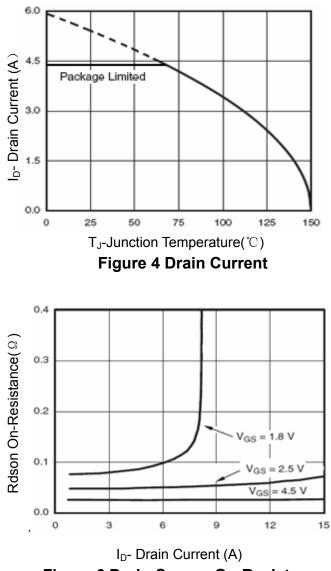


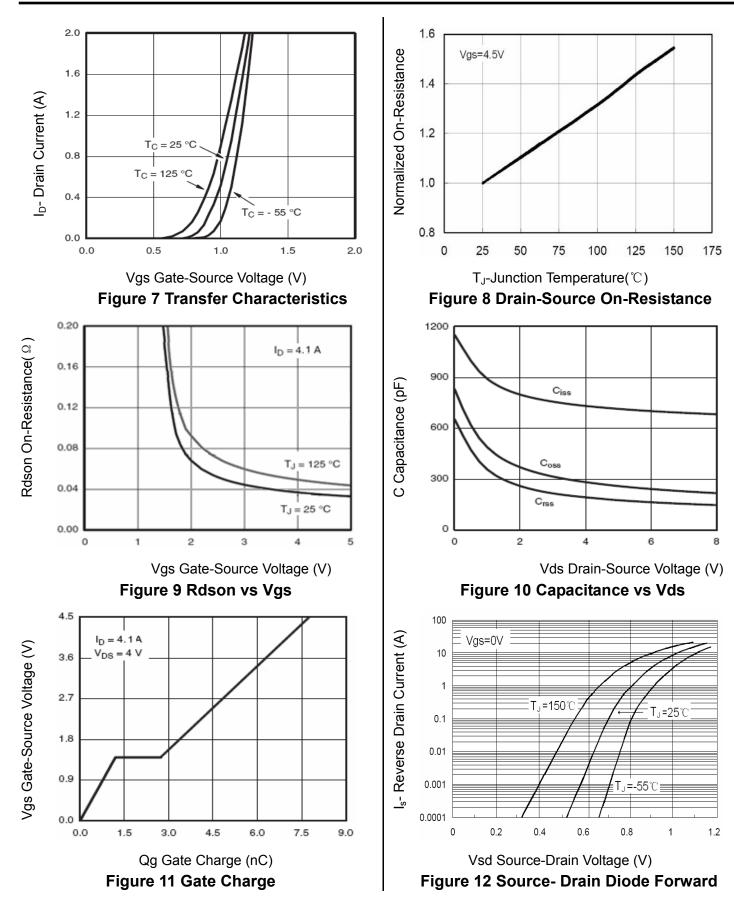
Figure 6 Drain-Source On-Resistance



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Pb Free Product

NCE2305A





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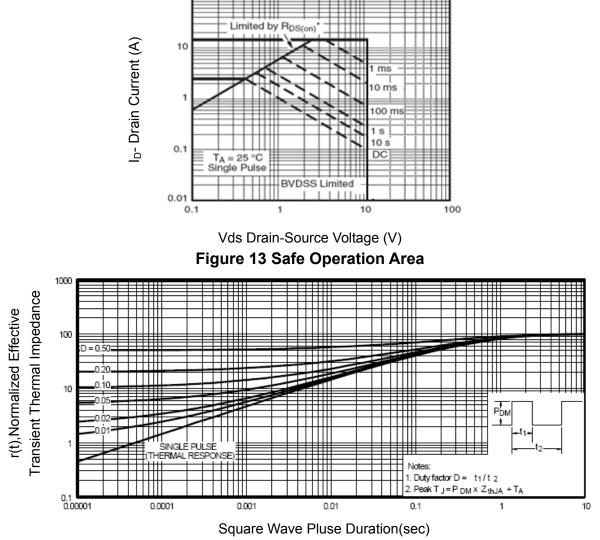


Figure 14 Normalized Maximum Transient Thermal Impedance

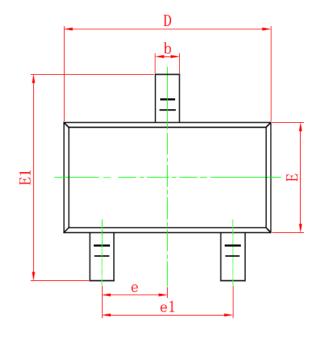


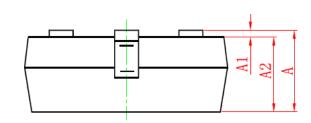
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SOT-23 Package Information





	<u>0. 25</u>
	<u> </u>

Symbol	Dimensions in Millimeters			
	MIN.	MAX.		
Α	0.900	1.150		
A1	0.000	0.100		
A2	0.900	1.050		
b	0.300	0.500		
С	0.080	0.150		
D	2.800	3.000		
Е	1.200	1.400		
E1	2.250	2.550		
е	0.950TYP			
e1	1.800	2.000		
L	0.550REF			
L1	0.300	0.500		
θ	0°	8°		

Notes

- 1. All dimensions are in millimeters.
- 2. Tolerance ± 0.10 mm (4 mil) unless otherwise specified
- 3. Package body sizes exclude mold flash and gate burrs. Mold flash at the non-lead sides should be less than 5 mils.
- 4. Dimension L is measured in gauge plane.
- 5. Controlling dimension is millimeter, converted inch dimensions are not necessarily exact.





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